

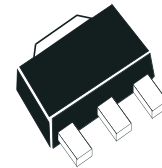
120V NPN SILICON HIGH VOLTAGE DARLINGTON TRANSISTOR

SUMMARY

$V_{CEO}=120V$; $V_{CE(sat)}= 1V$; $I_C= 1A$

DESCRIPTION

This new NPN Darlington transistor provides users with very efficient performance combining low $V_{CE(sat)}$ and very high H_{fe} to give extremely low on state losses at 120V operation. This makes it ideal for use in a variety of efficient driving functions including motors, lamps relays and solenoids and will also benefit circuits requiring high output current switching.



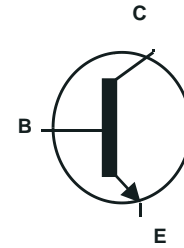
SOT 89

FEATURES

- Low Saturation Voltage
- **H_{fe}** min 2K @ 1A
- $I_C= 1A$ Continuous
- SOT89 package with Plot 1W
- Specification is also available in Eline and SOT223 package outlines

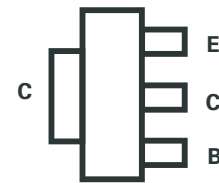
APPLICATIONS

- Various driving functions
 - Lamps
 - Motors
 - Relays and solenoids
- High output current switches



ORDERING INFORMATION

DEVICE	REEL SIZE (inches)	TAPE WIDTH (mm)	QUANTITY PER REEL
FCX605TA	7	12mm embossed	1000 units



Top View

DEVICE MARKING

605

FCX605

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	LIMIT NPN	UNIT
Collector-Base Voltage	V_{CBO}	140	V
Collector-Emitter Voltage	V_{CEO}	120	V
Emitter-Base Voltage	V_{EBO}	10	V
Peak Pulse Current	I_{CM}	4	A
Continuous Collector Current	I_C	1	A
Power Dissipation at $T_A=25^\circ\text{C}$ (a) Linear Derating Factor	P_D	1 8	W mW/ $^\circ\text{C}$
Power Dissipation at $T_A=25^\circ\text{C}$ (b) Linear Derating Factor	P_D	2.8 22	W mW/ $^\circ\text{C}$
Operating and Storage Temperature Range	$T_j:T_{stg}$	-55 to +150	$^\circ\text{C}$

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	125	$^\circ\text{C/W}$
Junction to Ambient (b)	$R_{\theta JA}$	45	$^\circ\text{C/W}$

NOTES

(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

(b) For a device surface mounted on FR4 PCB measured at $t \leq 5$ secs.

FCX605

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

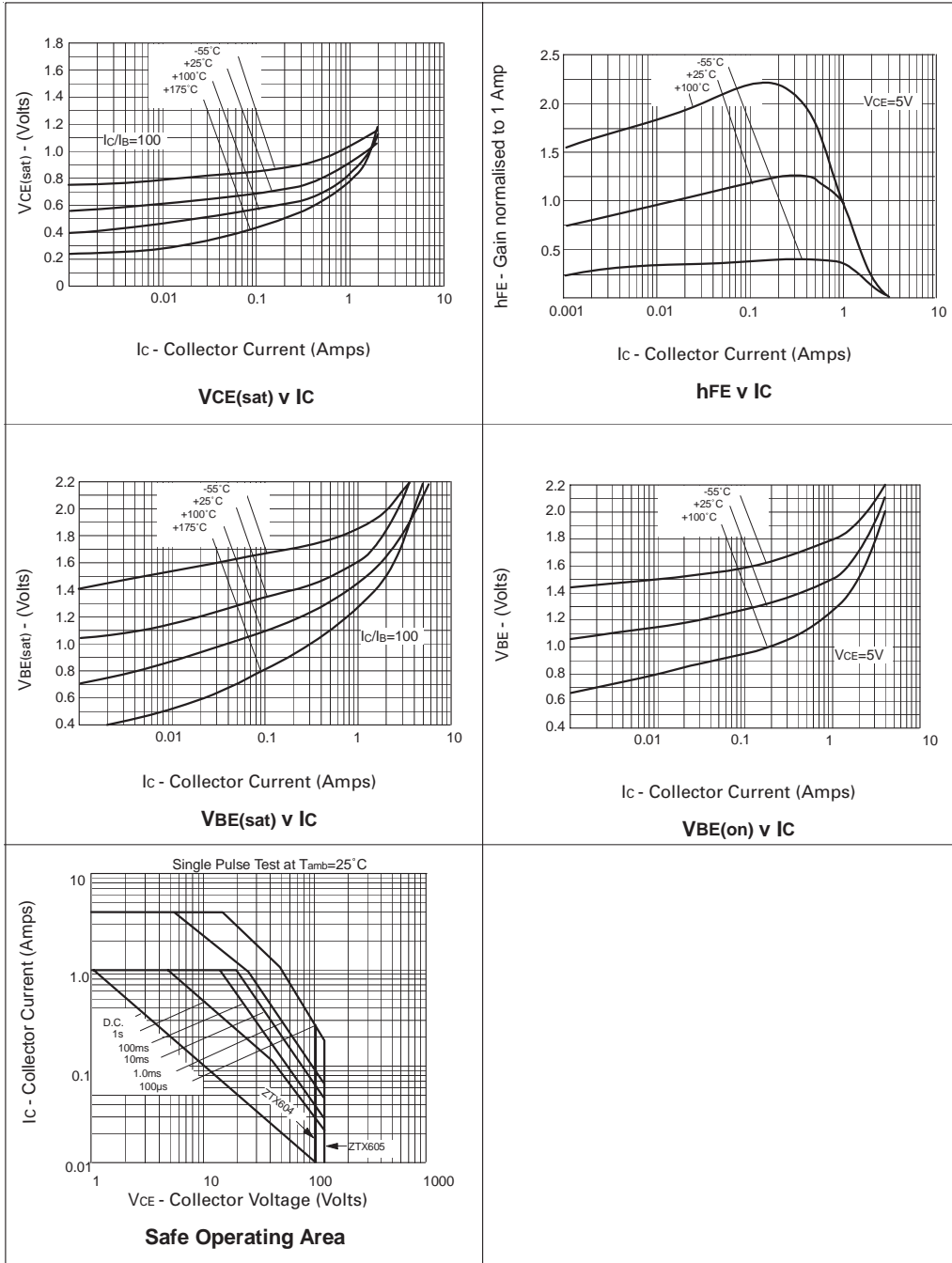
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	140			V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	120			V	$I_C = 10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	10			V	$I_E = 100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			100 10	nA μA	$V_{CB} = 10\text{V}$ $V_{CB} = 120\text{V}$ $T_{amb} = 100^{\circ}\text{C}$
Emitter Cut-Off Current	I_{EBO}			0.1	μA	$V_{EB} = 8\text{V}$
Collector Emitter Cut-Off Current	I_{CES}			10	μA	$V_{CES} = 120\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			1 1.5	V V	$I_C = 250\text{mA}, I_B = 0.25\text{mA}^*$ $I_C = 1\text{A}, I_B = 1\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			1.8	V	$I_C = 1\text{A}, I_B = 1\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			1.7	V	$I_C = 1\text{A}, V_{CE} = 5\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	2K 5K 2K 0.5	100K			$I_C = 50\text{mA}, V_{CE} = 5\text{V}^*$ $I_C = 500\text{mA}, V_{CE} = 5\text{V}^*$ $I_C = 1\text{A}, V_{CE} = 5\text{V}^*$ $I_C = 2\text{A}, V_{CE} = 5\text{V}^*$
Transition Frequency	f_T	150			MHz	$I_C = 100\text{mA}, V_{CE} = 10\text{V}$ $f = 20\text{MHz}$
Input Capacitance	C_{ibo}		90		pF	$V_{CB} = 500\text{mV}, f = 1\text{MHz}$
Output Capacitance	C_{obo}		15		pF	$V_{CB} = 10\text{V}, f = 1\text{MHz}$
Turn-On Time	$t_{(on)}$		0.5		μs	$I_C = 500\text{mA}, V_{CE} = 10\text{V}$ $I_{B1} = I_{B2} = 0.5\text{mA}$
Turn-Off Time	$t_{(off)}$		1.6		μs	$I_C = 500\text{mA}, V_{CE} = 10\text{V}$ $I_{B1} = I_{B2} = 0.5\text{mA}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

Nb. Spice parameter data is available upon request for this device.

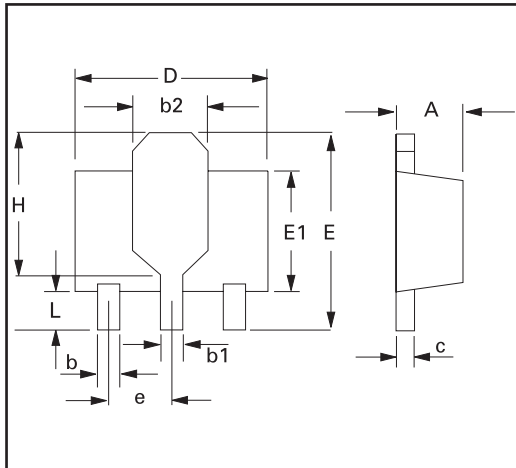
FCX605

NPN TYPICAL CHARACTERISTICS

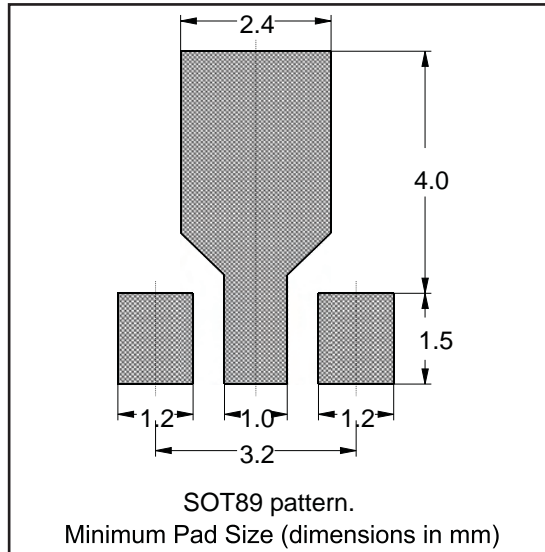


FCX605

PACKAGE DIMENSIONS



PAD LAYOUT DETAILS



PACKAGE DIMENSIONS

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	1.40	1.60	0.550	0.630	e	1.40	1.50	0.055	0.059
b	0.38	0.48	0.015	0.019	E	3.75	4.25	0.150	0.167
b1	-	0.53	-	0.021	E1	-	2.60	-	0.102
b2	1.50	1.80	0.060	0.071	G	2.90	3.00	0.114	0.118
c	0.28	0.44	0.011	0.017	H	2.60	2.85	0.102	0.112

© Zetex Semiconductors plc 2005

Europe	Americas	Asia Pacific	Corporate Headquarters
Zetex GmbH Streitfeldstraße 19 D-81673 München Germany	Zetex Inc 700 Veterans Memorial Hwy Hauppauge, NY 11788 USA	Zetex (Asia) Ltd 3701-04 Metroplaza Tower 1 Hing Fong Road, Kwai Fong Hong Kong	Zetex Semiconductors plc Zetex Technology Park Chadderton, Oldham, OL9 9LL United Kingdom
Telefon: (49) 89 45 49 49 0 Fax: (49) 89 45 49 49 49 europa.sales@zetex.com	Telephone: (1) 631 360 2222 Fax: (1) 631 360 8222 usa.sales@zetex.com	Telephone: (852) 26100 611 Fax: (852) 24250 494 asia.sales@zetex.com	Telephone (44) 161 622 4444 Fax: (44) 161 622 4446 hq@zetex.com

These offices are supported by agents and distributors in major countries world-wide.

This publication is issued to provide outline information only which (unless agreed by the Company in writing) may not be used, applied or reproduced for any purpose or form part of any order or contract or be regarded as a representation relating to the products or services concerned. The Company reserves the right to alter without notice the specification, design, price or conditions of supply of any product or service.

For the latest product information, log on to www.zetex.com

ISSUE 2 - SEPTEMBER 2005

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9